## **5LN01S**

# N-Channel Small Signal MOSFET 50V, 0.1A, 7.8Ω, Single SMCP



http://onsemi.com

### **Features**

- · Low ON-resistance
- · Ultrahigh-speed switching
- · 1.5V drive

### **Specifications**

### Absolute Maximum Ratings at Ta=25°C

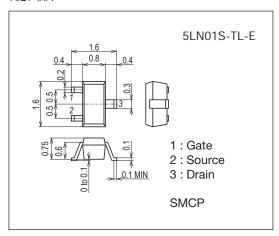
Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		50	V
Gate to Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	ID		0.1	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	0.4	А
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V", so please take care when handling.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### **Package Dimensions**

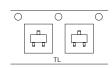
unit : mm (typ) 7027-004



### **Ordering & Package Information**

	•			
Device	Package	Shipping	memo	
5LN01S-TL-E	SMCP SC-75, SOT-416	3,000pcs./reel	Pb-Free	

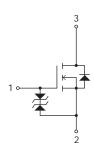
### Packing Type: TL



### Marking



### **Electrical Connection**



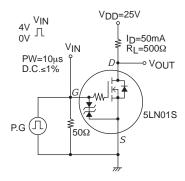
<sup>\*</sup> Machine Model

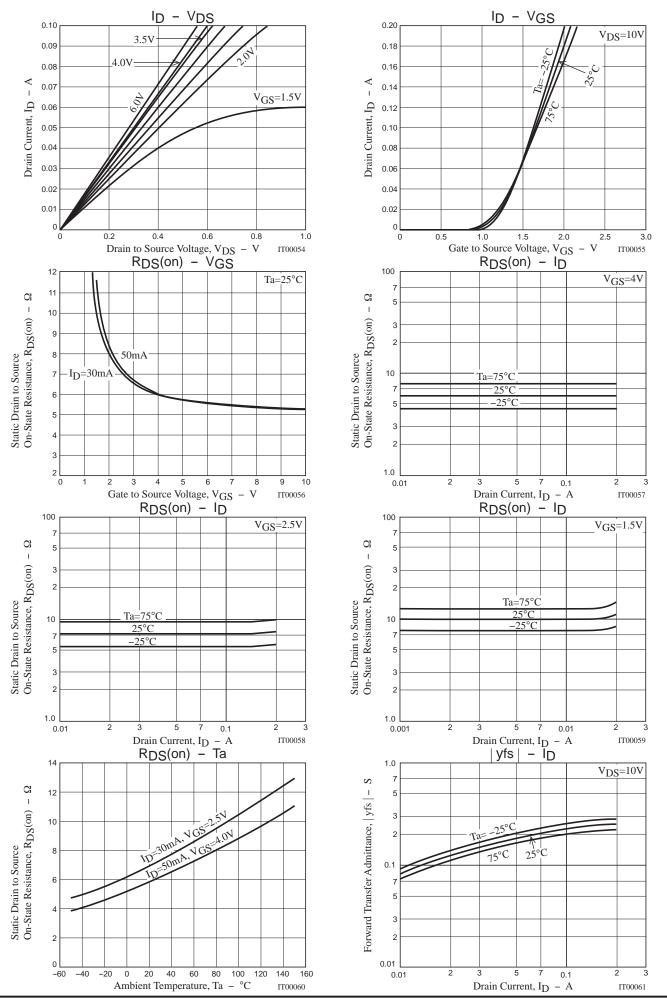
### 5LN01S

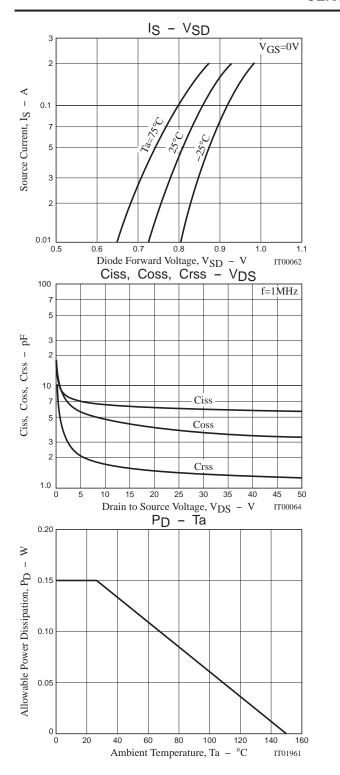
### Electrical Characteristics at Ta=25°C

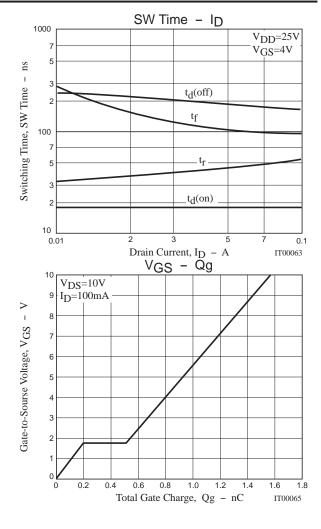
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	50			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =100μA	0.4		1.3	V
Forward Transfer Admittance	yfs	V <sub>D</sub> S=10V, I <sub>D</sub> =50mA	0.13	0.18		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =50mA, V <sub>GS</sub> =4V		6	7.8	Ω
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =30mA, V <sub>GS</sub> =2.5V		7.1	9.9	Ω
	R <sub>DS</sub> (on)3	I <sub>D</sub> =10mA, V <sub>GS</sub> =1.5V		10	20	Ω
Input Capacitance	Ciss			6.6		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		4.7		pF
Reverse Transfer Capacitance	Crss			1.7		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			18		ns
Rise Time	t <sub>r</sub>	Con an artificial Total Circuit		42		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		190		ns
Fall Time	tf			105		ns
Total Gate Charge	Qg			1.57		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =100mA		0.20		nC
Gate to Drain "Miller" Charge	Qgd			0.32		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =100mA, V <sub>GS</sub> =0V		0.85	1.2	V

### Switching Time Test Circuit







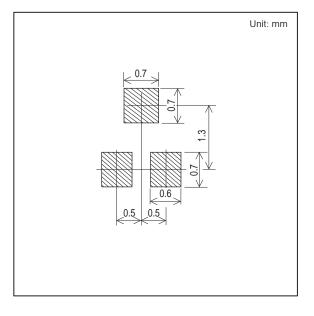


### **Outline Drawing**

5LN01S-TL-E

# | Mass (g) | Unit | 0.003 | rorreference | mm | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646 | 1 | 1.646

### Land Pattern Example



Note on usage: Since the 5LN01S is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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